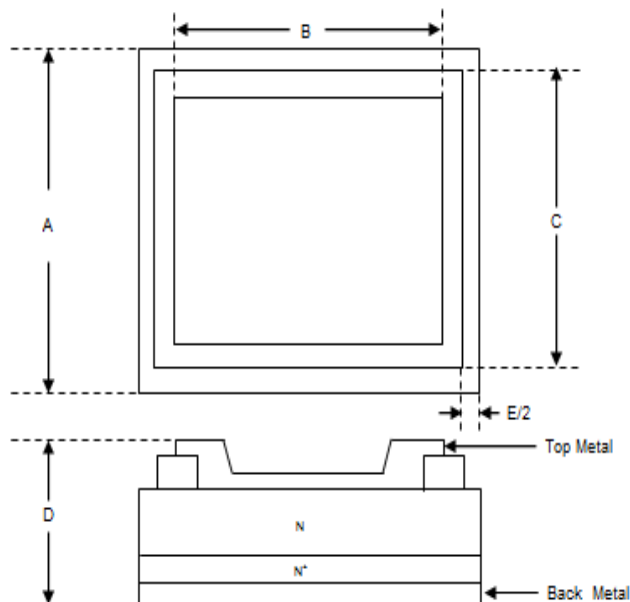


Planar MOS-Controlled Diode Wafer (PMCD)



| Item | Dimensions | |
|------------------------|------------|------|
| | um | mil |
| Die Size (A) | 2540 | 100 |
| Top Metal Pad Size (B) | 2330 | 91.7 |
| Passivation Seal (C) | 2480 | 97.6 |
| Wafer Thickness (D) | 260 | 10.2 |
| Scribe Line Width (E) | 60 | 2.36 |
| Other Informations | | |
| Wafer Size | 6" | |
| Gross Die | 2460 | |
| Top Metal | Ag | |
| Back Metal | Ag | |

| Electrical Characteristics @TA=25°C | | | | |
|---|-----------|---------------------------|---------------------|---------|
| Item | Symbol | Spec. Limit | Die Sort | Unit |
| Maximum Repetitive Peak Reverse Voltage @0.3mA | V_{RRM} | 45 | 51 | V |
| Maximum Average Forward Rectified Current | I_O | 15 | - | A |
| Forward Voltage Drop, @ $I_F=2A$ @ $I_F=5A$ @ $I_F=10A$ @ $I_F=15A$ | V_F | - 0.42 0.45 0.52 | 0.35 - - - | V |
| Maximum Reverse Current at Rated V_{RRM} | I_R | 130 | 110 | μA |
| Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC Method) | I_{FSM} | 250 | - | A |
| Operating Temperature Range | T_J | -50 to +150 | - | °C |
| Storage Temperature Range | T_{STG} | -50 to +150 | - | °C |
| ESD(IEC61000-4-2) | Contact | 20 | - | KV |